## BLF884P; BLF884PS UHF power LDMOS transistor Rev. 3 — 1 September 2015

**AMPLEON** 

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

A 350 W LDMOS RF power transistor for broadcast transmitter applications and industrial applications. The excellent ruggedness of this device makes it ideal for digital and analog transmitter applications.

Table 1. **Application information** 

RF performance at  $V_{DS}$  = 50 V unless otherwise specified.

Mode of operation	f	P <sub>L(AV)</sub>	P <sub>L(M)</sub>	Gp	$\eta_{D}$	IMD3	IMD <sub>shldr</sub>	PAR
	(MHz)	(W)	(W)	(dB)	(%)	(dBc)	(dBc)	(dB)
RF performance in a common source 860 MHz narrowband test circuit								
2-tone, class-AB	f <sub>1</sub> = 860; f <sub>2</sub> = 860.1	150	-	21	46	-32	-	-
DVB-T (8k OFDM)	858	70	-	21	33	-	-31 <mark>11</mark>	8.2 [2]
RF performance in a common source 470 MHz to 860 MHz broadband test circuit								
DVB-T (8k OFDM)	858	70	-	20	32	-	-32 [ <u>1]</u>	8.0 [2]

<sup>[1]</sup> Measured [dBc] with delta marker at 4.3 MHz from center frequency.

#### 1.2 Features and benefits

- Excellent ruggedness
- Optimum thermal behavior and reliability, R<sub>th(j-c)</sub> = 0.22 K/W
- High power gain
- High efficiency
- Designed for broadband operation (470 MHz to 860 MHz)
- Internal input matching for high gain and optimum broadband operation
- Excellent reliability
- Easy power control
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

#### 1.3 Applications

- Communication transmitter applications in the UHF band
- Industrial applications in the UHF band

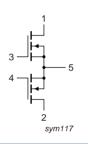
<sup>[2]</sup> PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.

## 2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLF884P	(SOT1121A)			
1	drain1			
2	drain2		1 2 [~] [~]	
3	gate1			3
4	gate2			5
5	source	[1]	3 4	2 sym117
BLF884P	S (SOT1121B)			Sylliti

# 1 drain1 2 drain2 3 gate1 4 gate2 5 source [1]



## 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BLF884P	-	flanged LDMOST ceramic package; 2 mounting holes; 4 leads	SOT1121A			
BLF884PS	-	earless flanged LDMOST ceramic package; 4 leads	SOT1121B			

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage		-	104	V
$V_{GS}$	gate-source voltage		-0.5	+11	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	200	°C

<sup>[1]</sup> Connected to flange.

#### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{\text{th(j-c)}}$	thermal resistance from junction to case	$T_{case} = 80  ^{\circ}C;  P_{L(AV)} = 70  W$	<u>11</u> 0.22	K/W

<sup>[1]</sup>  $R_{th(j-c)}$  is measured under RF conditions.

#### 6. Characteristics

Table 6. DC characteristics

 $T_i$  = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.2 \text{ mA}$	[1]	104	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS}$ = 10 V; $I_{D}$ = 120 mA	[1]	1.4	1.9	2.4	V
$I_{DSS}$	drain leakage current	$V_{GS}$ = 0 V; $V_{DS}$ = 50 V		-	-	1.4	μА
$I_{DSX}$	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$		-	19	-	Α
$I_{GSS}$	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}$		-	-	140	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 4.25 A$	[1]	-	240	-	mΩ
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	[2]	-	105	-	pF
C <sub>oss</sub>	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz		-	34	-	pF
C <sub>rss</sub>	reverse transfer capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz		-	0.7	-	pF

<sup>[1]</sup>  $I_D$  is the drain current.

Table 7. RF characteristics

RF characteristics in Ampleon production narrowband test circuit;  $T_{case} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
2-Tone, o	class-AB					
$V_{DS}$	drain-source voltage		-	50	-	V
I <sub>Dq</sub>	quiescent drain current	<u>I</u>	1] _	0.65	-	Α
$P_{L(AV)}$	average output power	$f_1 = 860 \text{ MHz};$ $f_2 = 860.1 \text{ MHz}$	150	-	-	W
G <sub>p</sub>	power gain	$f_1 = 860 \text{ MHz};$ $f_2 = 860.1 \text{ MHz}$	20	21	-	dB
$\eta_{D}$	drain efficiency	$f_1 = 860 \text{ MHz};$ $f_2 = 860.1 \text{ MHz}$	42	46	-	%
IMD3	third-order intermodulation distortion	f <sub>1</sub> = 860 MHz; f <sub>2</sub> = 860.1 MHz	-	-32	-28	dBc

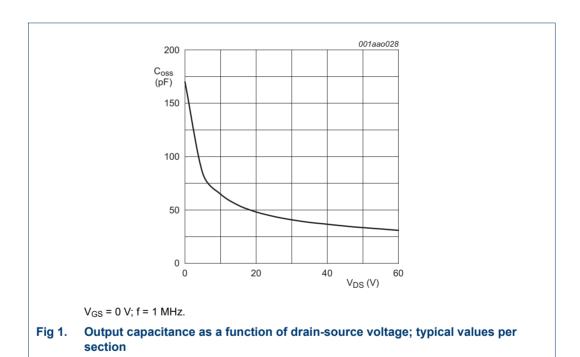
<sup>[2]</sup> Capacitance values without internal matching.

Table 7. RF characteristics ... continued

RF characteristics in Ampleon production narrowband test circuit;  $T_{case} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
DVB-T (8	k OFDM), class-AB						
$V_{DS}$	drain-source voltage			-	50	-	V
$I_{Dq}$	quiescent drain current		[1]	-	0.65	-	Α
$P_{L(AV)}$	average output power	f = 858 MHz		70	-	-	W
Gp	power gain	f = 858 MHz		20	21	-	dB
$\eta_{D}$	drain efficiency	f = 858 MHz		30	33	-	%
IMD <sub>shldr</sub>	intermodulation distortion shoulder	f = 858 MHz	[2]	-	-31	-27	dBc
PAR	peak-to-average ratio	f = 858 MHz	[3]	-	8.2	-	dB

- [1] I<sub>dq</sub> for total device
- [2] Measured [dBc] with delta marker at 4.3 MHz from center frequency.
- [3] PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.



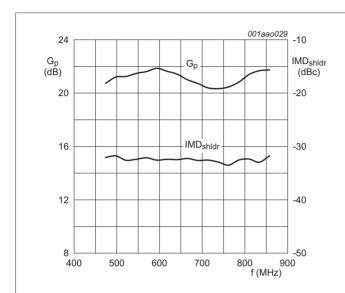
#### 6.1 Ruggedness in class-AB operation

The BLF884P and BLF884PS are capable of withstanding a load mismatch corresponding to VSWR of  $\geq$  40 : 1 through all phases under the following conditions:  $V_{DS}$  = 50 V; f = 860 MHz at rated power.

## 7. Application information

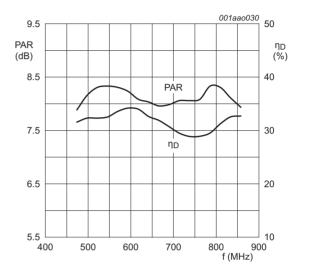
#### 7.1 Broadband RF figures

#### 7.1.1 DVB-T



 $P_{L(AV)}=70$  W;  $V_{DS}=50$  V;  $I_{Dq}=0.65$  A; measured in a common source broadband test circuit as described in Section 8.

Fig 2. DVB-T power gain and intermodulation distortion shoulder as function of frequency; typical values



 $P_{L(AV)}$  = 70 W;  $V_{DS}$  = 50 V;  $I_{Dq}$  = 0.65 A; measured in a common source broadband test circuit as described in Section 8

Fig 3. DVB-T peak-to-average ratio and drain efficiency as function of frequency; typical values

## 7.2 Impedance information

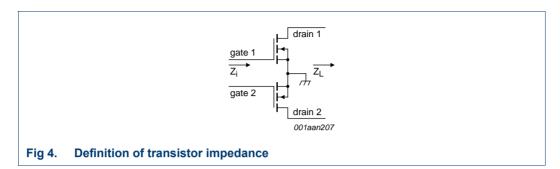


Table 8. Typical push-pull impedance

Simulated  $Z_i$  and  $Z_L$  device impedance; impedance info at  $V_{DS} = 50 \text{ V}$  and  $P_{L(AV)} = 70 \text{ W}$  (DVB-T).

f	<b>Z</b> i	$\mathbf{Z_L}$
MHz	Ω	Ω
300	0.984 – j3.485	8.315 + j1.246
325	1.009 – j2.805	8.236 + j1.328
350	1.038 – j2.185	8.153 + j1.406
375	1.071 – j1.614	8.066 + j1.479
400	1.107 – j1.080	7.975 + j1.547
425	1.147 – j0.574	7.880 + j1.610
450	1.193 – j0.092	7.782 + j1.667
475	1.243 + j0.373	7.682 + j1.720
500	1.300 + j0.826	7.579 + j1.767
525	1.364 + j1.270	7.474 + j1.809
550	1.436 + j1.708	7.367 + j1.846
575	1.517 + j2.144	7.258 + j1.877
600	1.609 + j2.581	7.149 + j1.903
625	1.714 + j3.022	7.038 + j1.925
650	1.834 + j3.469	6.927 + j1.941
675	1.971 + j3.925	6.815 + j1.952
700	2.129 + j4.394	6.703 + j1.958
725	2.313 + j4.879	6.591 + j1.960
750	2.528 + j5.382	6.480 + j1.956
775	2.781 + j5.907	6.368 + j1.949
800	3.081 + j6.458	6.258 + j1.937
825	3.441 + j7.038	6.148 + j1.921
850	3.875 + j7.648	6.040 + j1.901
875	4.404 + j8.291	5.932 + j1.877
900	5.057 + j8.964	5.825 + j1.849
925	5.870 + j9.659	5.720 + j1.818
950	6.892 + j10.358	5.616 + j1.783
975	8.186 + j11.019	5.514 + j1.745
1000	9.829 + j11.566	5.413 + j1.704

## 8. Test information

Table 9. List of components

For test circuit, see Figure 5 and Figure 6.

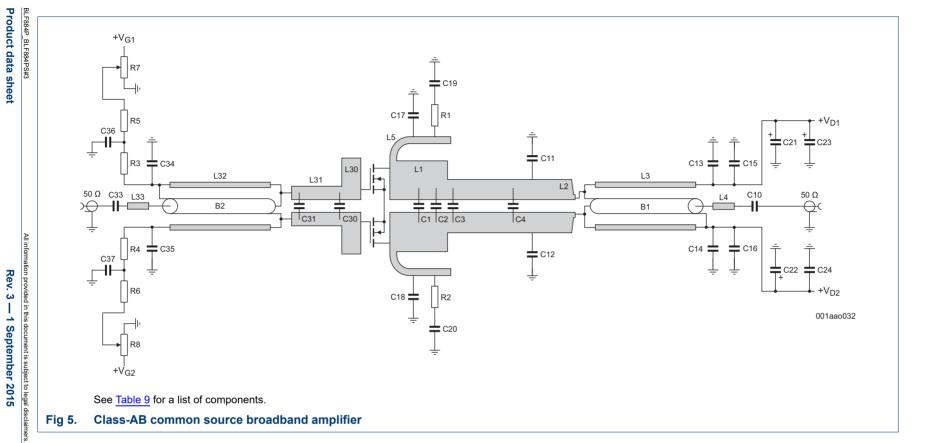
Component	Description	Value		Remarks
B1, B2	semi rigid coax	25 Ω; 49.5 mm		UT-090C-25 (EZ 90-25)
C1, C2	multilayer ceramic chip capacitor	5.1 pF	<u>[1]</u>	
C3	multilayer ceramic chip capacitor	6.8 pF	<u>[1]</u>	
C4	multilayer ceramic chip capacitor	8.2 pF	<u>[1]</u>	
C10, C13, C14	multilayer ceramic chip capacitor	100 pF	[2]	
C11, C12	multilayer ceramic chip capacitor	10 pF	<u>[1]</u>	
C15, C16	multilayer ceramic chip capacitor	4.7 μF, 50 V		Kemet C1210X475K5RAC-TU or capacitor of same quality.
C17, C18, C23, C24	multilayer ceramic chip capacitor	100 pF	<u>[1]</u>	
C19, C20	multilayer ceramic chip capacitor	10 μF, 50 V		TDK C570X7R1H106KT000N or capacitor of same quality.
C21, C22	electrolytic capacitor	470 μF; 63 V		
C30	multilayer ceramic chip capacitor	13 pF	[3]	
C31	multilayer ceramic chip capacitor	2.2 pF	[3]	
C33, C34, C35	multilayer ceramic chip capacitor	100 pF	[3]	
C36, C37	multilayer ceramic chip capacitor	4.7 μF, 50 V		TDK C4532X7R1E475MT020U or capacitor of same quality.
L1	microstrip	-	<u>[4]</u>	(W $\times$ L) 15 mm $\times$ 13 mm
L2	microstrip	-	[4]	(W $\times$ L) 5 mm $\times$ 26 mm
L3, L32	microstrip	-	<u>[4]</u>	(W $\times$ L) 2 mm $\times$ 49.5 mm
L4	microstrip	-	<u>[4]</u>	(W $\times$ L) 1.7 mm $\times$ 3.5 mm
L5	microstrip	-	<u>[4]</u>	(W $\times$ L) 2 mm $\times$ 9.5 mm
L30	microstrip	-	<u>[4]</u>	(W $\times$ L) 5 mm $\times$ 13 mm
L31	microstrip	-	<u>[4]</u>	(W $\times$ L) 2 mm $\times$ 11 mm
L33	microstrip	-	[4]	(W $\times$ L) 2 mm $\times$ 3 mm
R1, R2	wire resistor	10 Ω		
R3, R4	SMD resistor	5.6 Ω		0805
R5, R6	wire resistor	100 Ω		
R7, R8	potentiometer	10 kΩ		

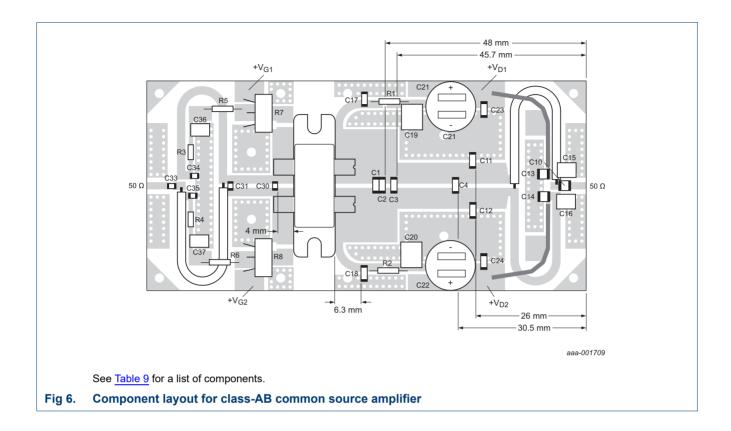
<sup>[1]</sup> American technical ceramics type 800B or capacitor of same quality.

<sup>[2]</sup> American technical ceramics type 180R or capacitor of same quality.

<sup>[3]</sup> American technical ceramics type 100A or capacitor of same quality.

<sup>[4]</sup> Printed-Circuit Board (PCB): Taconic RF35;  $\varepsilon_r$  = 3.5 F/m; height = 0.762 mm; Cu (top/bottom metallization); thickness copper plating = 35  $\mu$ m.





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## 9. Package outline

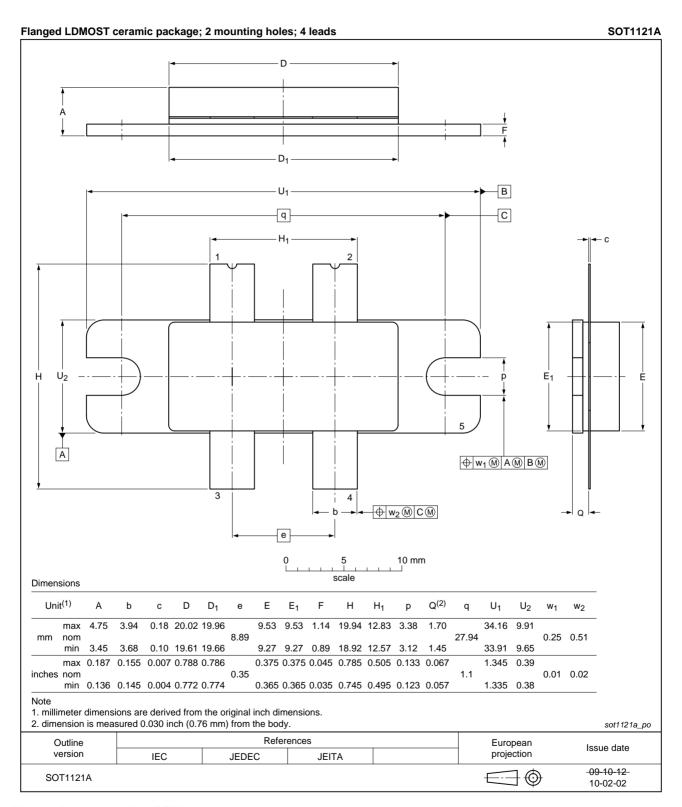


Fig 7. Package outline SOT1121A

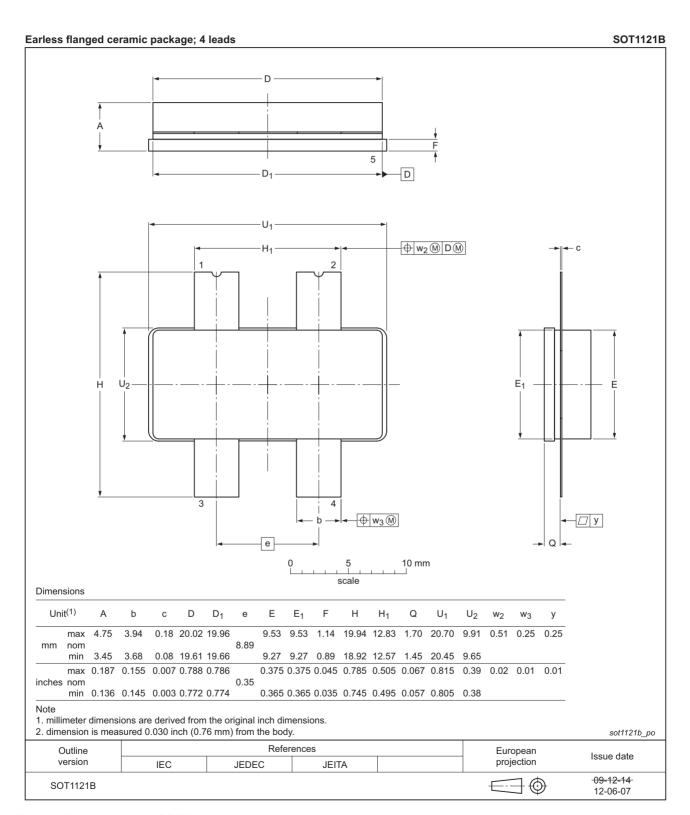


Fig 8. Package outline SOT1121B

BLF884P; BLF884PS

**UHF power LDMOS transistor** 

## 10. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

## 11. Abbreviations

Table 10. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
DVB	Digital Video Broadcast
DVB-T	Digital Video Broadcast - Terrestrial
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
OFDM	Orthogonal Frequency Division Multiplexing
PAR	Peak-to-Average power Ratio
RF	Radio Frequency
SMD	Surface Mounted Device
UHF	Ultra High Frequency
VSWR	Voltage Standing-Wave Ratio

## 12. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BLF884P_BLF884PS#3	20150901	Product data sheet	-	BLF884P_BLF884PS v.2		
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of Ampleon.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>					
BLF884P_BLF884PS v.2	20111216	Product data sheet	-	BLF884P_BLF884PS v.1		
BLF884P_BLF884PS v.1	20111013	Objective data sheet	-	-		

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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## BLF884P; BLF884PS

**UHF power LDMOS transistor** 

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